UNI-SEMICONDUCTOR CO.,LTD

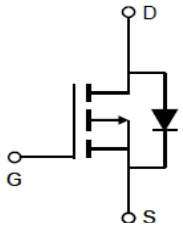
宇 力 半 导 体 有 限 公 司

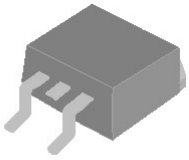
AP90P03K Data Sheet

V 1.1

Features

- V_{DS}=-30V I_D (at V_{GS}=10V)= -90A
- $R_{DS(ON)}$ (at V_{GS}=10V) < 7.5m Ω
- $R_{DS(ON)}$ (at V_{GS}=4.5V) < 12mΩ
- Trench Power Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for Fast-switching Applications





TO-252(H)

Applications

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage (V_{GS} = 0V)		V_{DSS}	-30	V
Continuous Drain Current	T_C = 25ºC	I_D	-90	A
	T_C = 100ºC		-63	
Pulsed Drain Current (note1)		I_{DM}	-360	A
Gate-Source Voltage		V_{GSS}	±20	V
Single Pulse Avalanche Energy (note2)		E_{AS}	135	mJ
Avalanche Current		I_{As}	-30	A
Power Dissipation (note3)	T_C = 25ºC	P_D	79	W
	T_C = 100ºC		39.5	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+175	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	2.5	ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	

Specifications T_J = 25°C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-30	–	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -30V, V_{GS} = 0V, T_J = 25°C	–	–	-1	μA
		V_{DS} = -30V, V_{GS} = 0V, T_J = 100°C	–	–	-25	
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	–	–	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.0	-1.7	-2.4	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	V_{GS} = -10V, I_D = -20A	–	6.3	7.5	mΩ
		V_{GS} = -4.5V, I_D = -20A	–	10	12	mΩ
Forward Transconductance (Note3)	g_{fs}	V_{DS} = -5V, I_D = -20A	30	–	--	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -15V, f = 1.0MHz	–	4942	--	pF
Output Capacitance	C_{oss}		–	473	--	
Reverse Transfer Capacitance	C_{rss}		–	461	--	
Total Gate Charge	Q_g	V_{DD} = -15V, I_D = -20A, V_{GS} = -10V	–	82	--	nC
Gate-Source Charge	Q_{gs}		–	14	--	
Gate-Drain Charge	Q_{gd}		–	16	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = -15V, I_D = -20A, R_G = 2.5Ω	–	182	--	ns
Turn-on Rise Time	t_r		–	262	--	
Turn-off Delay Time	$t_{d(off)}$		–	1.3	--	
Turn-off Fall Time	t_f		–	9.8	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25°C	–	–	-90	A
Pulsed Diode Forward Current	I_{SM}		–	–	-360	
Body Diode Voltage	V_{SD}	T_J = 25°C, I_{SD} = -15A, V_{GS} = 0V	–	–	-1.2	V
Reverse Recovery Time	t_{rr}	I_F = -15A, di_F/dt = 100A/μs	–	34	--	ns
Reverse Recovery Charge	Q_{rr}		–	79	--	nC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_{AS} = -30A, L=0.3mH,V_{DD} = 30V, R_G = 25Ω, Starting T_J = 25°C
3. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

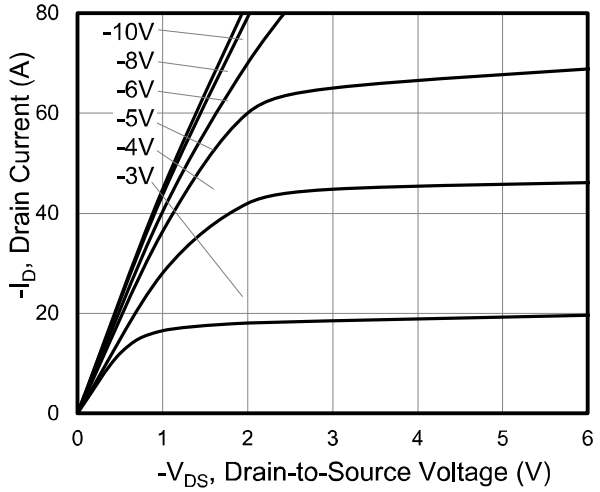


Figure 2. Transfer Characteristics

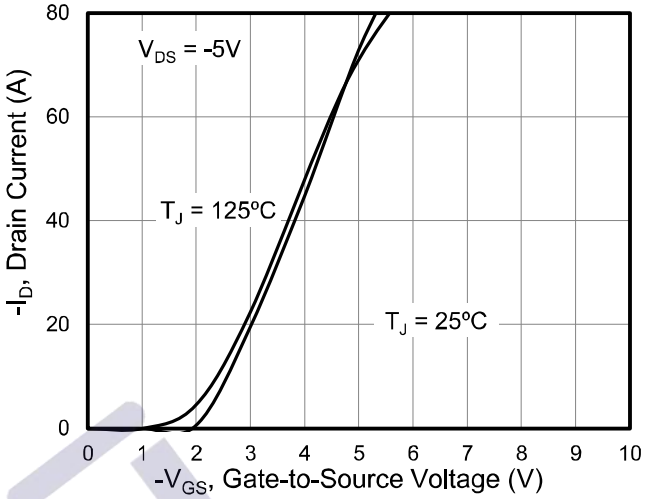


Figure 3. On-Resistance vs. Drain Current

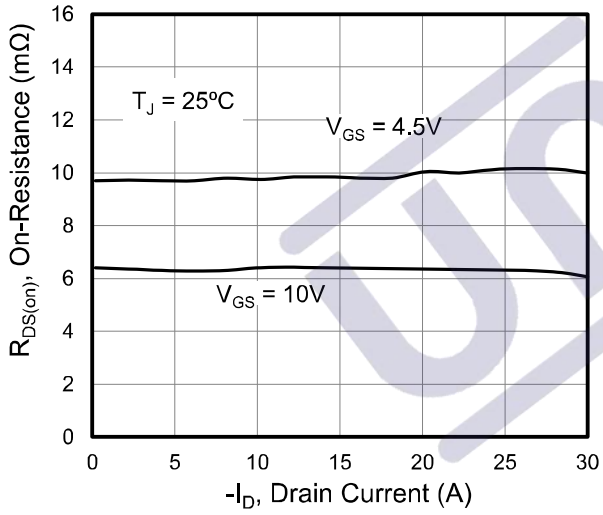


Figure 4. Capacitance

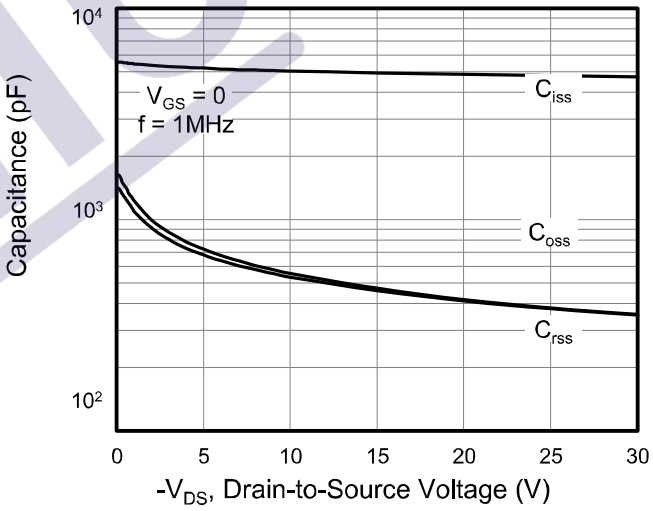


Figure 5. Gate Charge

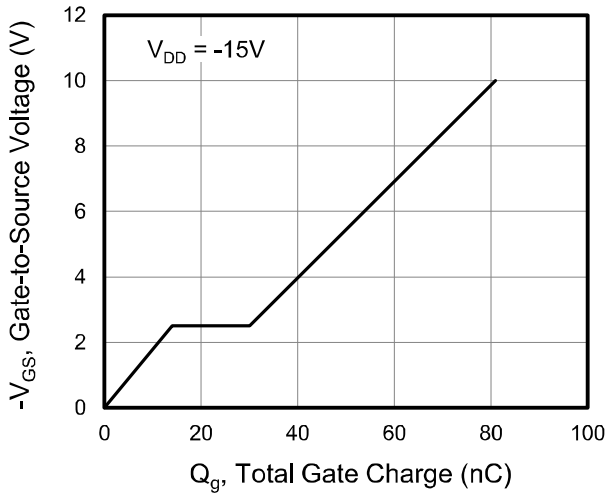
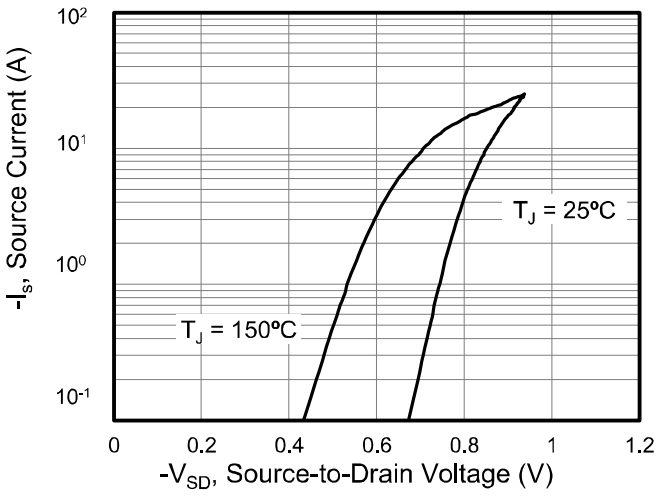


Figure 6. Body Diode Forward Voltage



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

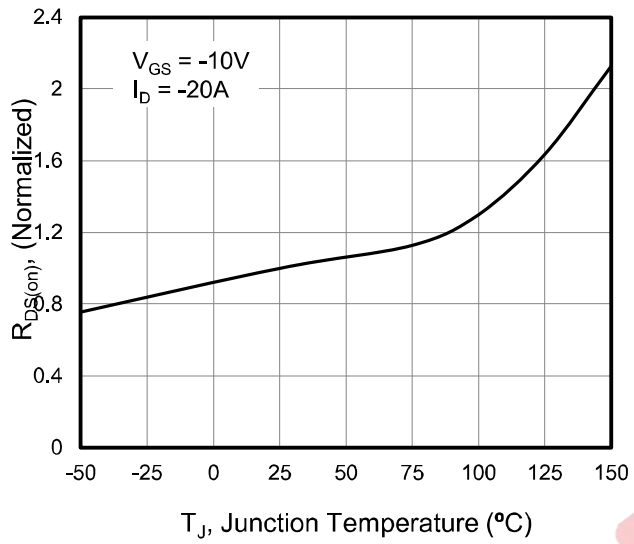


Figure 8. Threshold Voltage vs. Junction Temperature

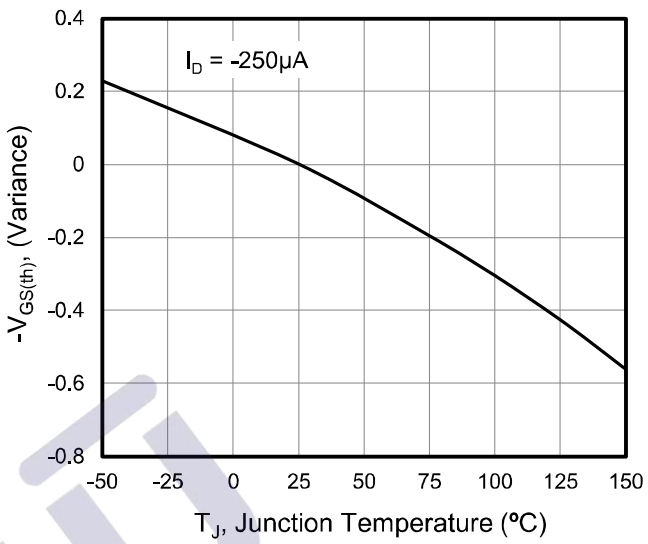


Figure 9. Transient Thermal Impedance

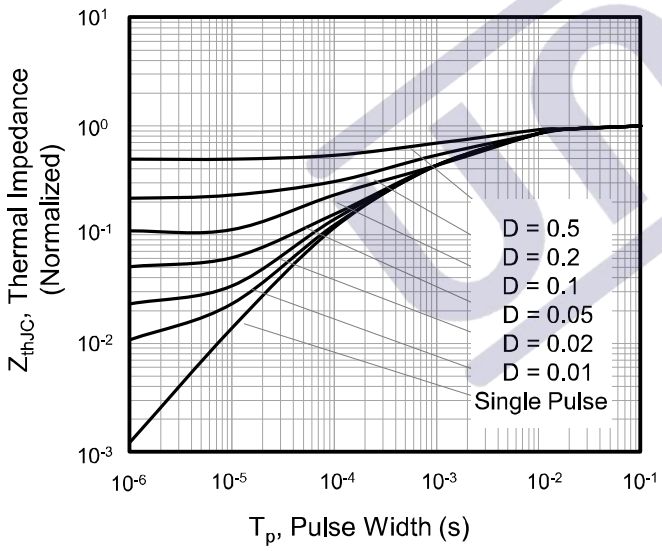


Figure 10. Safe operation area

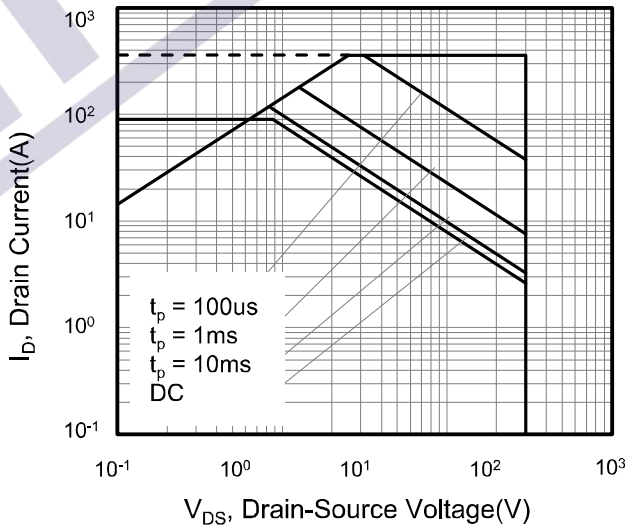


Figure A：Gate Charge Test Circuit and Waveform

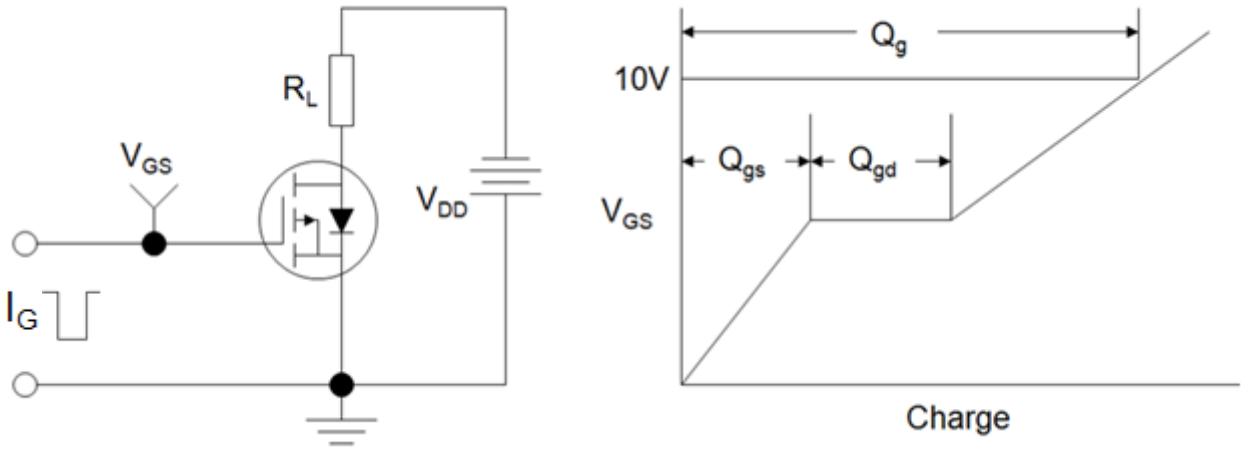


Figure B：Resistive Switching Test Circuit and Waveform

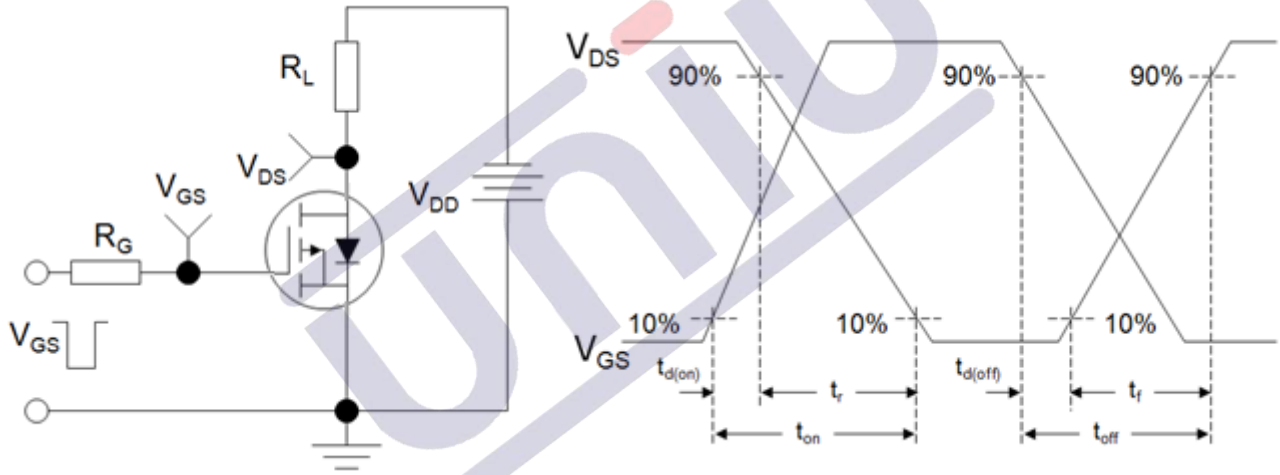
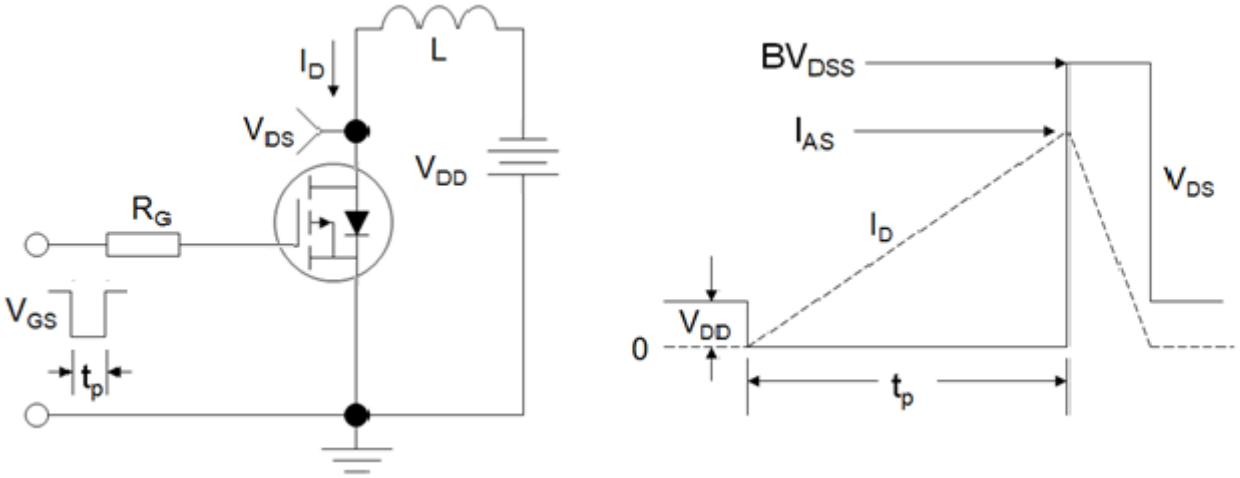


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



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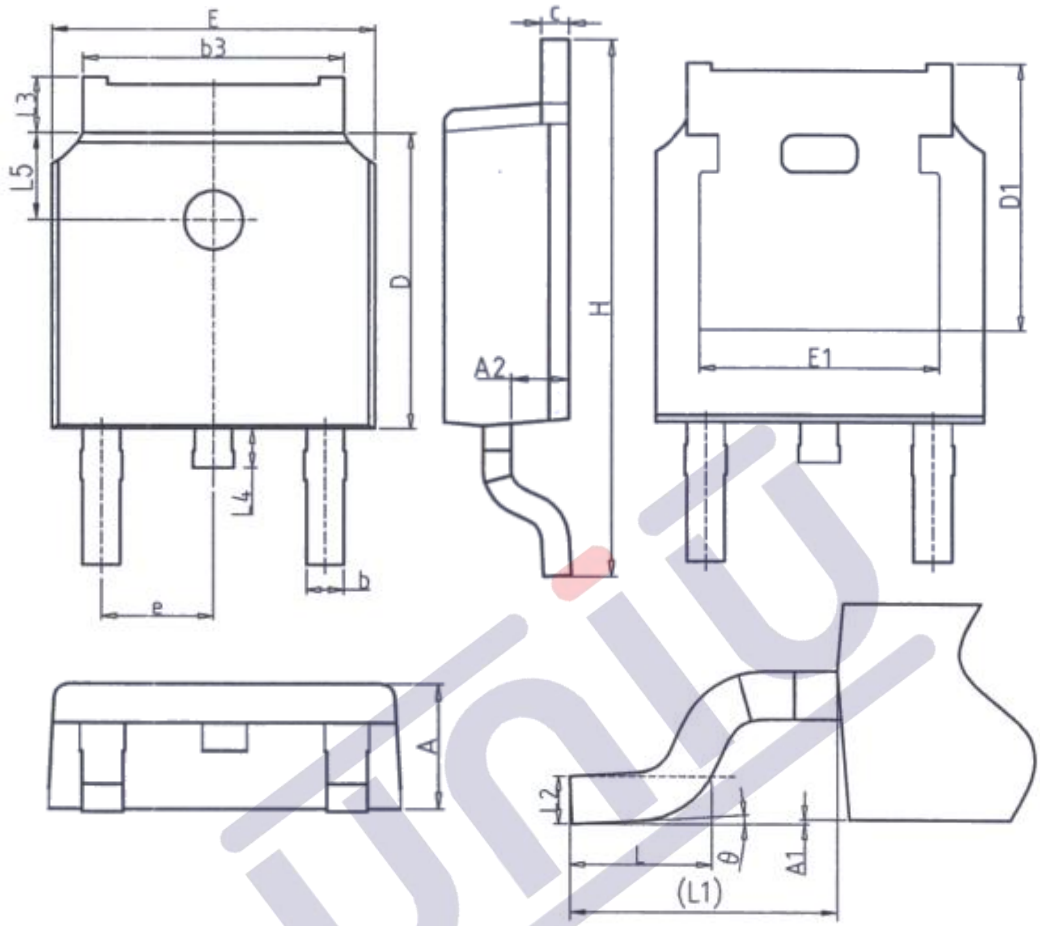

Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	–

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	–	1.00
L5	1.65	1.95
θ	0°	8°

1.版本记录

DATE	REV.	DESCRIPTION
2018/04/19	1.0	First Release
2021/11/10	1.1	Layout adjustment

2.免责声明

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浙江宇力微新能源科技有限公司

总部地址：绍兴市越城区斗门街道袍渎路25号中节能科创园45幢4/5楼 电话：0575-85087896（研发部）

传真：0575-88125157

E-mail: htw@uni-semic.com

无锡地址：无锡市锡山区先锋中路 6 号中国电子（无锡）数字芯城 1#综合楼 503室

电 话 : 0510-85297939

E-mail: zh@uni-semic.com

深圳地址：深圳市宝安区西乡街道南昌社区宝源路泳辉国际商务大厦410

电 话 ： 0755-84510976

E-mail: htw@uni-semic.com